MPSA144

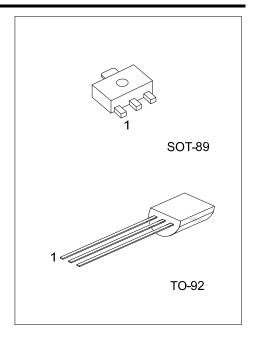
**Preliminary** 

## NPN SILICON TRANSISTOR

# **HIGH VOLTAGE TRANSISTOR**

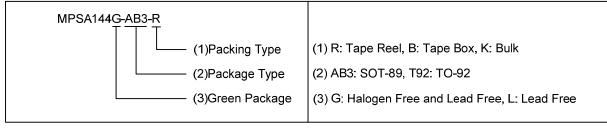
#### **■ FEATURES**

- \* Collector-Emitter Voltage:
- \* V<sub>CEO</sub>=500V
- \* Collector Current up to 300mA

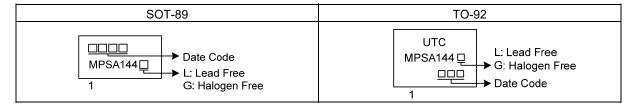


#### **■ ORDERING INFORMATION**

Ordering Number		Daalaana	Pin Assignment			Da alaina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MPSA144L-AB3-R	MPSA144G-AB3-R	SOT-89	В	С	Е	Tape Reel	
MPSA144L-T92-B	MPSA144G-T92-B	TO-92	Е	В	C	Tape Box	
MPSA144L-T92-K	MPSA144G-T92-K	TO-92	E	В	С	Bulk	



#### ■ MARKING



www.unisonic.com.tw 1 of 3

### ABSOLUTE MAXIMUM RATING

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		$V_{CBO}$	500	V
Collector-Emitter Voltage		$V_{CEO}$	500	V
Emitter-Base Voltage		$V_{EBO}$	6	V
Collector Current		lc	300	mA
Collector Dissipation(T <sub>A</sub> =25°C)	SOT-89	1	500	mW
	TO-92	Pc	625	mW
Operating Junction Temperature		$T_J$	-40 ~ +150	°C
Storage Temperature		T <sub>STG</sub>	-40 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## **■ THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	SOT-89	0	250	°C/W	
	TO-92	θJA	200	°C/W	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

## ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BVcBo	Ic=100µA, IE=0	500	1 11	IVIAX	V
Collector-Emitter Breakdown Voltage	BVCBO	Ic=1mA, Iв=0	500			V
•	BVEBO		6			V
Emitter-Base Breakdown Voltage		I <sub>E</sub> =100μA, I <sub>C</sub> =0	0		0.4	<u> </u>
Collector-Base Cutoff Current	Ісво	Vcb=500V, IE=0			0.1	μA
Collector Cutoff Current	Ices	Vce=500V, I <sub>B</sub> =0			0.5	μA
Emitter-Base Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.1	μΑ
ON CHARACTERISTICS						
	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	80			
DO 0 10 : (N. I.)		V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	82			
DC Current Gain (Note)		V <sub>CE</sub> =10V, I <sub>C</sub> =50mA	45			
		V <sub>CE</sub> =10V, I <sub>C</sub> =100mA	20			
		I <sub>C</sub> =1mA, I <sub>B</sub> =0.1mA			0.4	٧
Collector-Emitter Saturation Voltage	VCE(SAT)	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.5	٧
		I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.75	٧
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	Ic=10mA, I <sub>B</sub> =1mA			0.75	V
SMALL-SIGNAL CHARACTERISTICS	•	·	•	•	•	
Current Gain Bandwidth Product	f⊤	V <sub>CE</sub> =20V,I <sub>C</sub> =10mA, f=100MHz	50			MHz

Note: Pulse test: PW<300 $\mu$ s, Duty Cycle<2%

<sup>2.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

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